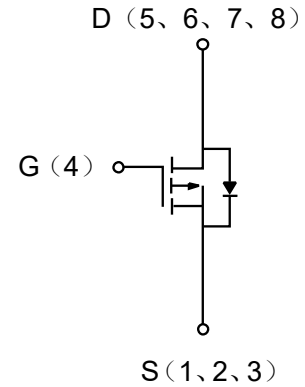


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
-30	0.011 @ V _{GS} =-10V	-11
	0.015 @ V _{GS} =-4.5V	


Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = -250μA, V _{GS} = 0V	-30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.7		-3.0	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = -10V, I _D = -9.1A	-	11	15	mΩ
		V _{GS} = -4.5V, I _D = -7A	-	15	20	mΩ
Forward Tran conductance	g _{FS}	V _{GS} = -5V, I _D = -5A, T _A = 125°C		26		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz	-	2900		pF
Output Capacitance	C _{DSS}		-	500		pF
Reverse Transfer Capacitance	C _{RSS}		-	140		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DD} = -15V, V _{GS} = -10V, R _L = 1.25Ω, R _G = 3Ω, I _D = -1A	-	12.4		ns
Turn-Off Delay Time	t _{d(off)}		-	8.2		ns

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	-11	A
	Pulsed	I_D	-40	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	P_D	3	W
	$T_A=125^\circ\text{C}$	P_D	2.1	W

Typical Characteristics

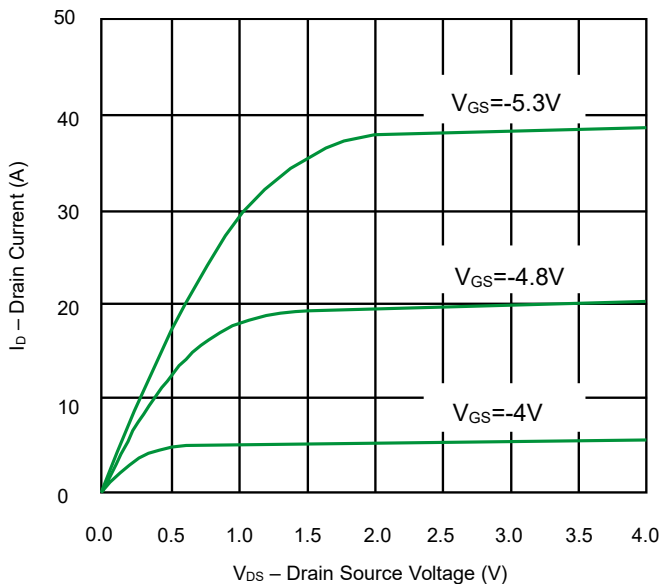


Fig 1. Output Characteristics

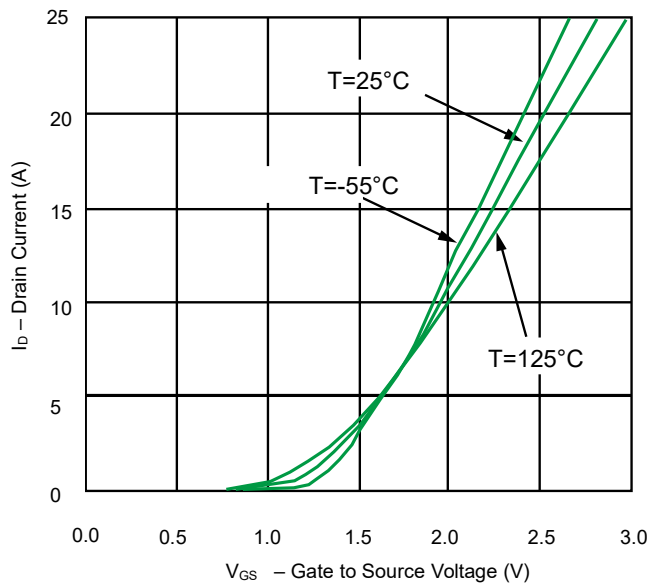


Fig 2. Transfer Characteristics

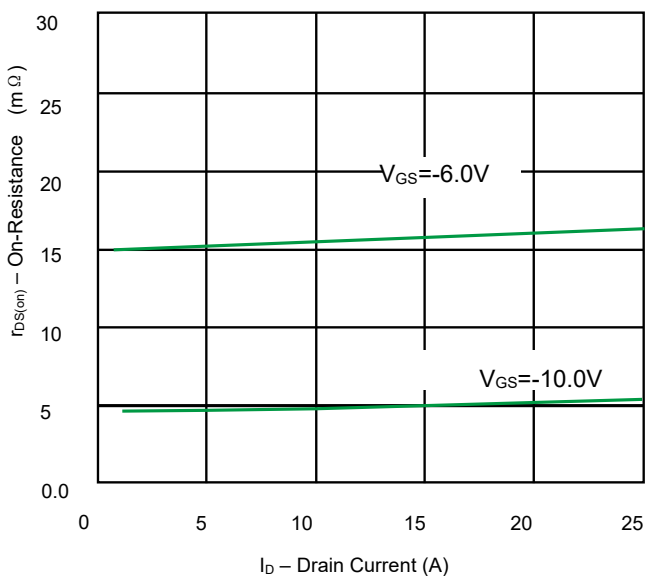


Fig 3. On-Resistance vs. Drain Current

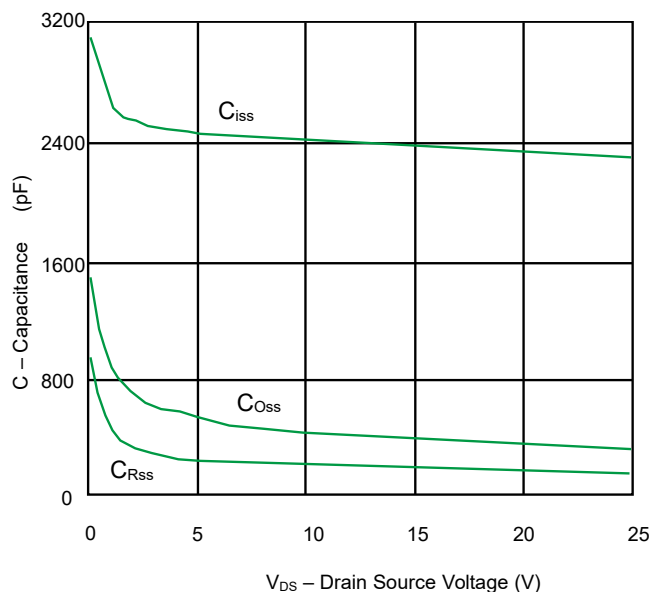
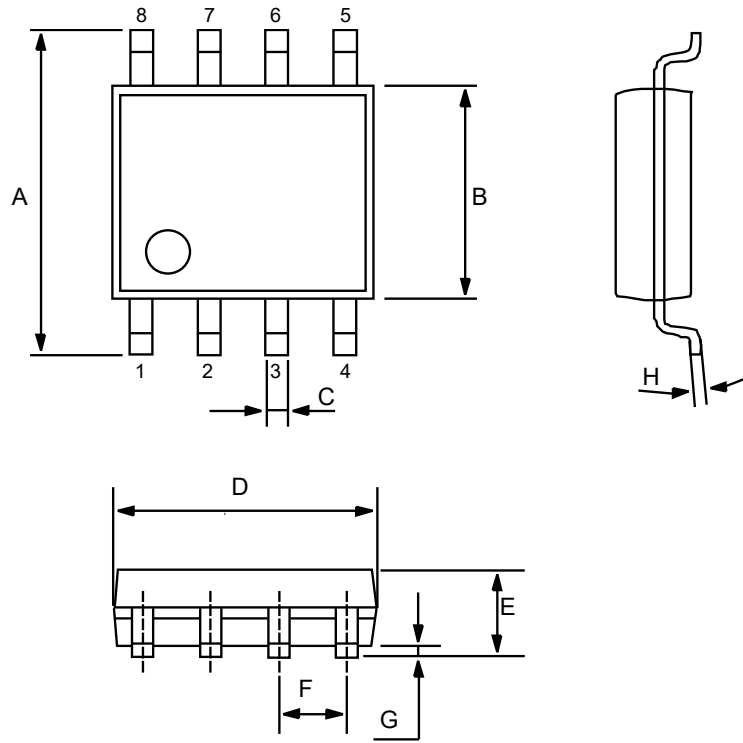



Fig 4. Capacitance

Product dimension (SOP-8)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	5.800	6.200	0.228	0.244
B	3.800	4.000	0.150	0.157
C	0.330	0.510	0.013	0.020
D	4.700	5.100	0.185	0.200
E	1.350	1.750	0.053	0.069
F	1.270 (BSC)		0.050 (BSC)	
G	0.100	0.250	0.004	0.010
H	0.170	0.250	0.006	0.010


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